

Absolute rate constants for the reaction of silylene with

Journal of Chemical Physics

88, 1678-1687

DOI: 10.1063/1.454146

Citation Report

#	ARTICLE	IF	CITATIONS
1	Chemiluminescence during thermal chemical vapour deposition of SiO ₂ from silane-oxygen mixtures. Chemical Physics Letters, 1988, 153, 33-38.	2.6	13
2	Gas phase and surface reactions in Si doping of GaAs by silanes. Journal of Crystal Growth, 1988, 93, 594-601.	1.5	41
3	The role of surface reactions in monosilane pyrolysis. Journal of Chemical Physics, 1988, 89, 2544-2549.	3.0	54
4	a-Si:H Deposition from SiH ₄ and Si ₂ H ₆ rf-Discharges: Pressure and Temperature Dependence of Film Growth in Relation to \hat{I}_{\pm} -I ³ Discharge Transition. Japanese Journal of Applied Physics, 1988, 27, 2041-2052.	1.5	110
5	Effects of Substrate Temperature and Gas Phase Chemistry on the APCVD of a Si:H Films From Disilane. Materials Research Society Symposia Proceedings, 1988, 118, 97.	0.1	0
6	Excimer Laser Photodissociation Studies of Disilane AT 193 nm. Materials Research Society Symposia Proceedings, 1988, 131, 487.	0.1	5
7	Laser CVD of A-Si:H: Film Properties and Mechanism. Materials Research Society Symposia Proceedings, 1988, 131, 495.	0.1	2
8	Production of disilane and silyl sticking coefficients during plasma-enhanced chemical vapor deposition of hydrogenated amorphous silicon. Applied Physics Letters, 1989, 54, 1642-1644.	3.3	13
9	Sticking coefficient of the SiH ₂ free radical on a hydrogenated silicon-carbon surface. Applied Physics Letters, 1989, 54, 185-187.	3.3	23
10	Atom and radical surface sticking coefficients measured using resonance-enhanced multiphoton ionization. Journal of Chemical Physics, 1989, 91, 5037-5049.	3.0	27
11	Mass Spectrometric Studies on Silicon Doping of OMYPE GaAs. Japanese Journal of Applied Physics, 1989, 28, 1298-1306.	1.5	16
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13	Precision surface temperature measurement and film characterization for LICVD of a-Si: H from SiH ₄ . Applied Surface Science, 1989, 36, 81-88.	6.1	7
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16	Quantum yield studies of disilane photodissociation at 193 nm by infrared diode laser spectroscopy. Chemical Physics Letters, 1989, 155, 576-582.	2.6	21
17	Influence of dilution in nitrogen on the photodissociation processes of silane and disilane at 193 nm. Applied Surface Science, 1989, 43, 17-22.	6.1	3
18	Some considerations of the thermodynamics and kinetics of the chemical vapour deposition of tungsten. Applied Surface Science, 1989, 38, 312-337.	6.1	42

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20	Controversies in the suggested mechanisms of plasma-induced deposition of silicon from silane. Thin Solid Films, 1989, 175, 129-139.	1.8	36
21	Transport phenomena and chemical reaction issues in OMVPE of compound semiconductors. Journal of Crystal Growth, 1989, 98, 148-166.	1.5	59
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